4-Pin Full Pitch Mini-Flat Package Phototransistor Optocouplers

FODM121 Series, FODM124, FODM2701, FODM2705

Description

The FODM121 series, FODM124, and FODM2701 consists of a gallium arsenide infrared emitting diode driving a phototransistor in a compact 4–pin mini–flat package. The lead pitch is 2.54 mm. The FODM2705 consists of two gallium arsenide infrared emitting diodes connected in inverse parallel for AC operation.

Features

- More than 5 mm Creepage/Clearance
- Compact 4-Pin Surface Mount Package (2.4 mm Maximum Standoff Height)
- Current Transfer Ratio in Selected Groups:
 - ♦ DC Input:
 - FODM121: 50–600%
 FODM121A: 100–300%
 FODM121B: 50–150%
 FODM121C: 100–200%
 FODM124: 100% MIN
 - FODM124: 100% MINFODM2701: 50–300%
 - AC Input:
 - FODM2705: 50-300%
- Safety and Regulatory Approvals:
 - ◆ UL1577, 3,750 VAC_{RMS} for 1 Minute
 - ◆ DIN-EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage
- This Device is Pb-Free and is RoHS Compliant

Applications

- Digital Logic Inputs
- Microprocessor Inputs
- Power Supply Monitor
- Twisted Pair Line Receiver
- Telephone Line Receiver



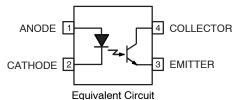
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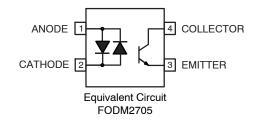


MFP4 3.85X4.4, 2.54P CASE 100AP

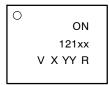
PIN CONNECTIONS



Equivalent Circuit FODM121, FODM124, FODM2701



MARKING DIAGRAM



ON = ON Semiconductor Logo

121xx = Device Number

V = DIN EN/IEC60747-5-5 Option

X = One-Digit Year Code
YY = Digit Work Week
R = Assembly Package Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

SAFETY AND INSULATION RATINGS

As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics	
Installation Classifications per DIN VDE 0110/1.89.	< 150 V _{RMS}	I–IV	
For Rated Mains Voltage	< 300 V _{RMS}	I–III	
Climatic Classification		40/110/21	
Pollution Degree (DIN VDE 0110/1.89)		2	
Comparative Tracking Index		175	

Symbol	Parameter	Value	Unit
V _{PR}	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	904	V _{peak}
	Input-to-Output Test Voltage, Method B, V _{IORM} x 1.875 = V _{PR} , 100% Production Test with t _m = 1 s, Partial Discharge < 5 pC	1060	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	565	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	6000	V _{peak}
	External Creepage	≥ 5	mm
	External Clearance	≥ 5	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T _S	Case Temperature (Note 1)	150	°C
I _{S,INPUT}	Input Current (Note 1)	200	mA
P _{S,OUTPUT}	Output Power (Note 1)	300	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V (Note 1)	> 10 ⁹	Ω

^{1.} Safety limit values – maximum values allowed in the event of a failure.

ABSOLUTE MAXIMUM RATINGS T_A = 25°C Unless otherwise specified.

Symbol		Value	Unit	
TOTAL PACK	AGE			•
T _{STG}	Storage Temperature	-40 to +125	°C	
T _{OPR}	Operating Temperature	Operating Temperature		°C
TJ	Junction Temperature		-40 to +125	°C
T _{SOL}	Lead Solder Temperature		260 for 10 s	°C
EMITTER				
I _{F (avg)}	Continuous Forward Current	50	mA	
I _{F (pk)}	Peak Forward Current (1 μs pul	1	А	
V_{R}	Reverse Voltage		6	V
P_{D}	Power Dissipation Derate linearly (Above 75°C)		70	mW
			1.41	mW/°C
DETECTOR				
I _C	Continuous Collector Current		80	mA
V_{CEO}	Collector-Emitter Voltage	FODM121 Series, FODM124	80	V
		FODM2701, FODM2705	40	
V _{ECO}	Emitter-Collector Voltage		7	V
P_{D}	Power Dissipation	150	mW	
	Derate linearly (Above 80°C)	3.27	mW/°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS T_A = 25°C Unless otherwise specified.

Symbol	Parameter	Device	Test Conditions	Min	Тур	Max	Unit
INDIVIDUA	L COMPONENT CHARACTERIS	TICS			-	_	
Emitter							
V _F	Forward Voltage	FODM121 Series, FODM124	I _F = 10 mA	1.0	-	1.3	V
		FODM2701	I _F = 5 mA		-	1.4	
		FODM2705	$I_F = \pm 5 \text{ mA}$				
I _R	Reverse Current	FODM121 Series, FODM124, FODM2701	V _R = 5 V	_	-	5	μΑ
Detector					-	_	
BV _{CEO}	Collector-Emitter Breakdown Voltage	FODM121 Series, FODM124	I _C = 1 mA, I _F = 0	80	-	-	V
		FODM2701, FODM2705		40	-	-	
BV _{ECO}	Emitter-Collector Breakdown Voltage	All	$I_E = 100 \mu A, I_F = 0$	7	-	-	V
I _{CEO}	Collector Dark Current	All	V _{CE} = 40 V, I _F = 0	-	-	100	nA
C _{CE}	Capacitance	All	V _{CE} = 0 V, f = 1 MHz	-	10		pF
	R CHARACTERISTICS		•			_	
CTR	DC Current Transfer Ratio	FODM2701	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	50	_	300	%
		FODM2705	$I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V}$	50	_	300	
		FODM121	I _F = 5 mA, V _{CE} = 5 V	50	-	600	
		FODM121A		100	_	300	
		FODM121B		50	-	150	
		FODM121C		100	-	200	
		FODM124	I _F = 1 mA, V _{CE} = 0.5 V	100	-	1200	
			I _F = 0.5 mA, V _{CE} = 1.5 V	50	-	-	
	CTR Symmetry	FODM2705	$I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V}$	0.3	_	3.0	
V _{CE(SAT)}	Saturation Voltage	FODM121 Series	$I_F = 8 \text{ mA}, I_C = 2.4 \text{ mA}$	-	_	0.4	V
,		FODM124	$I_F = 1 \text{ mA}, I_C = 0.5 \text{ mA}$	-	-	0.4	
		FODM2701	I _F = 10 mA, I _C = 2 mA	-	_	0.3	
		FODM2705	$I_F = \pm 10 \text{ mA}, I_C = 2 \text{ mA}$	-	-	0.3	
t _r	Rise Time (Non-Saturated)	All	I_C = 2 mA, V_{CE} = 5 V, R_L = 100 Ω	-	3	-	μs
t _f	Fall Time (Non-Saturated)	All	I_C = 2 mA, V_{CE} = 5 V, R_L = 100 Ω	_	3	-	μs
SOLATION	N CHARACTERISTICS						
V _{ISO}	Steady State Isolation Voltage (Note 2)	All	1 minute	3750	-	-	VAC _{RN}

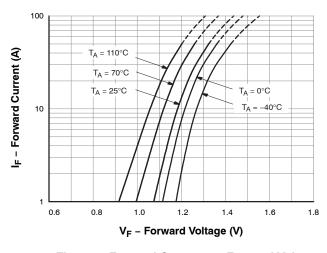
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Steady state isolation voltage, V_{ISO}, is an internal device dielectric breakdown rating. For this test, pins 1 and 2 are common, and pins 3 and

Steady state isolation voltage, V_{ISO}, is an internal device dielectric breakdown rating. For this test, pins 1 and 2 are common, and pins 3 and 4 are common.

TYPICAL PERFORMANCE CURVES

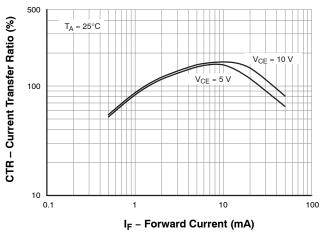
(T_A = 25°C unless otherwise specified)



0.35 0.30 V_{CE(sat)} - Collector-Emitter Saturation Voltage (V) 0.25 $I_F = 8 \text{ mA}$ = 2.4. mA 0.20 0.15 $I_F = 10 \text{ mA}$ I_C = 2 mA 0.10 0.05 0.00 -40 -20 20 60 120 40 80 100 T_A - Ambient Temperature (°C)

Figure 1. Forward Current vs. Forward Voltage

Figure 2. Collector–Emitter Saturation Voltage vs. Ambient Temperature (FODM121/2701/2705)



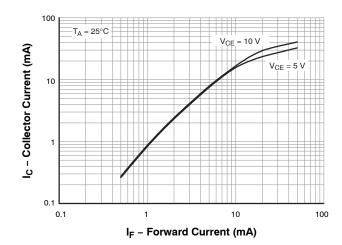
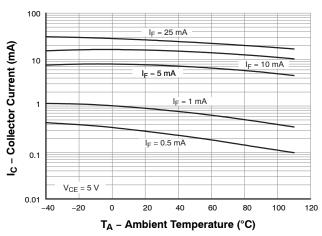


Figure 3. Current Transfer Ratio vs. Forward Current (FODM121/2701/2705)

Figure 4. Collector Current vs. Forward Current (FODM121/2701/2705)



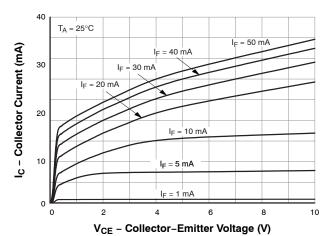


Figure 5. Collector Current vs. Ambient Temperature (FODM121/2701/2705)

Figure 6. Collector Current vs. Ambient Temperature (FODM121/2701/2705)

TYPICAL PERFORMANCE CURVES (Continued)

(T_A = 25°C unless otherwise specified)

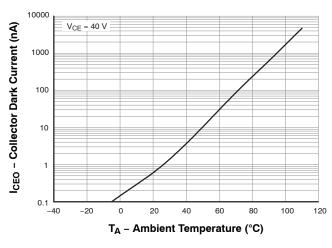


Figure 7. Collector Dark Current vs. Ambient Temperature (FODM121/2701/2705)

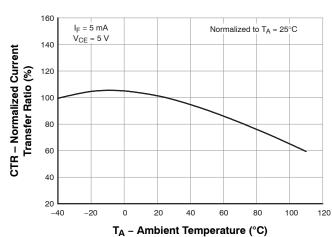


Figure 8. Normalized Current Transfer Ratio vs. Ambient Temperature (FODM121/2701/2705)

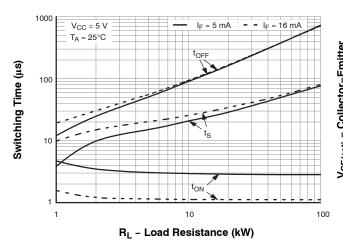


Figure 9. Switching Time vs. Load Resistance (FODM121/2701/2705)

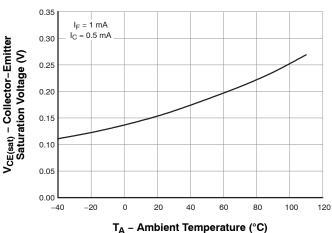


Figure 10. Collector–Emitter Saturation Voltage vs. Ambient Temperature (FODM124)

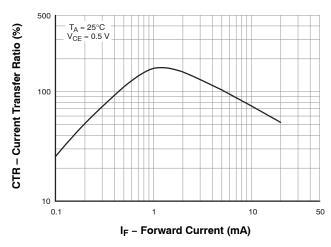


Figure 11. Current Transfer Ratio vs. Forward Current (FODM124)

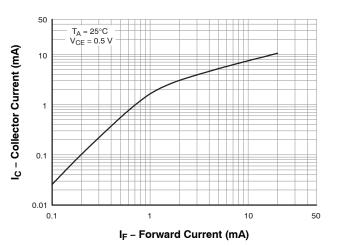


Figure 12. Collector Current vs. Forward Current (FODM124)

TYPICAL PERFORMANCE CURVES (Continued)

(T_A = 25°C unless otherwise specified)

I_C - Collector Current (mA)

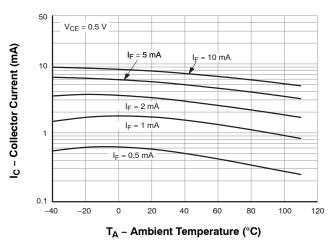
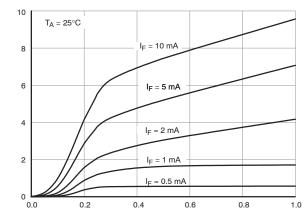


Figure 13. Collector Current vs. Ambient Temperature (FODM124)



V_{CE} - Collector-Emitter Voltage (V)

Figure 14. Collector Current vs. Collector-Emitter Voltage (FODM124)

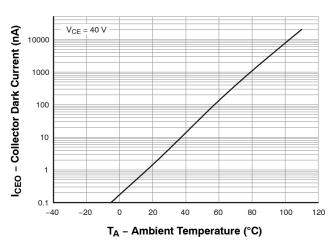


Figure 15. Collector Dark Current vs. Ambient Temperature (FODM124)

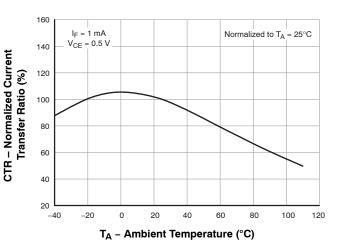


Figure 16. Normalized Current Transfer Ratio vs. Ambient Temperature (FODM124)

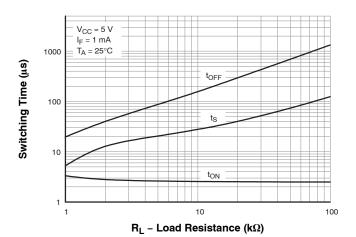
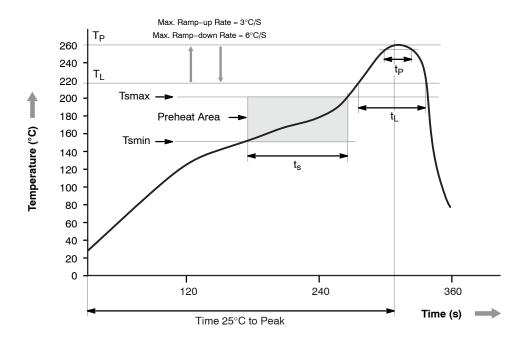


Figure 17. Switching Time vs. Load Resistance (FODM124)

REFLOW PROFILE



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60–120 s
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidus Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60–150 s
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 s
Ramp-down Rate (T _P to T _L)	6°C/s max.
Time 25°C to Peak Temperature	8 min max.

ORDERING INFORMATION

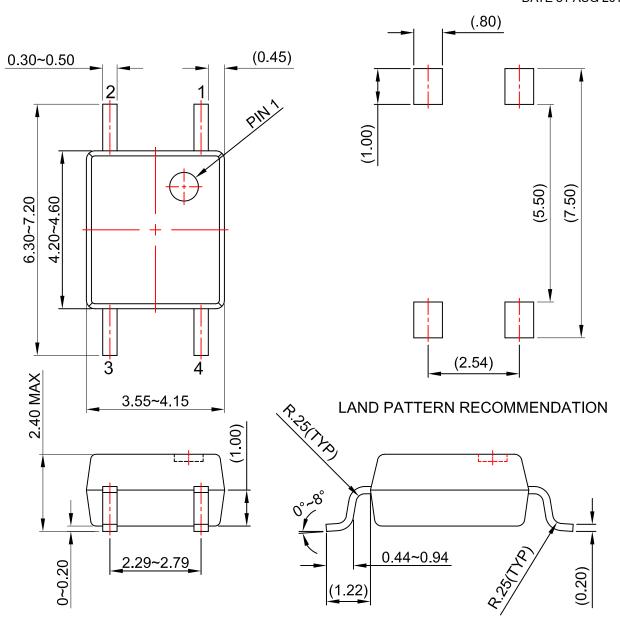
Part Number (Note 3)	Package	Shipping [†]
FODM121	Full Pitch Mini-Flat 4-Pin	100 / Tube
FODM121R2	Full Pitch Mini-Flat 4-Pin	2,500 / Tape and Reel
FODM121V	Full Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	100 / Tube
FODM121R2V	Full Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	2,500 / Tape and Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{3.} The product orderable part number system listed in this table also applies to the FODM121A, FODM121B, FODM121C, FODM124, FODM2701, and FODM2705 products.

MFP4 3.85X4.4, 2.54P CASE 100AP ISSUE O

DATE 31 AUG 2016



NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION

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FODM124R2 FODM2705R2 FODM121C FODM121BR2V FODM121CR2V FODM121B FODM2705V FODM121BV

FODM121A FODM121AR2V FODM121AV FODM121CV FODM121AR2 FODM121BR2 FODM121CR2

FODM2705R2V FODM124R2V FODM121V FODM2701R4